## **ELECTRONIC INFORMATION DISCLOSURE STATEMENT**

Electronic Version v18 Stylesheet Version v18.0

Title of Invention

METHOD FOR FORMING DAMASCENE STRUCTURE UTILIZING PLANARIZING MATERIAL COUPLED WITH DIFFUSION BARRIER MATERIAL

Confirmation Number:

First Named Applicant: William Wille

Attorney Docket Number: FIS920030024US1

Search string:

(6316167 or 20020164877 or 20010036748 or 20020012876 ).pn.

<u>Certification:</u> This Information Disclosure Statement was submitted under the following conditions, which satisfies the requirement under 37 CFR 1.97(e). The filer certified:

That each item of information contained in the information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement.

## **US Patent Documents**

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
E	1	6316167	2001-11-13	Angelopoulos, et al.			

## **US Published Applications**

Note: Applicant is not required to submit a paper copy of cited US Published Applications

init	Cite.No.	Pub. No.	Date	Applicant	Kind	Class	Subclass
EG	1	20020164877	2002-11-07	Catabay, et al.			
	2	20010036748	2001-11-01	Rutter, Jr., et al.			
V	3	20020012876	2002-01-31	Angelopoulos, et al.			.0

Signature Lew 1/13/05

Examiner Name Date

		Docket Number (Optional)	Application Number			
IPE		FIS920030024US1	Application Number 10/604,056			
O, INE	RMATION DISCLOSURE CITATION (Use several theets if necessary)	Applicant(s) William Wille, et al.				
SEP 2 2 2003	N	Filing Date	Group Art Unit			
	ğ	6/24/03				
EXAMINER OF	OTHER DOCUMENTS (Including Author, Tit					
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considered. Include copy of this form with next communication to applicant.

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INITIAL		DOCUMENT NUMBER	DATE	<del></del>	NAME	CDGS	300000	IF APPROPRIATE		
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